

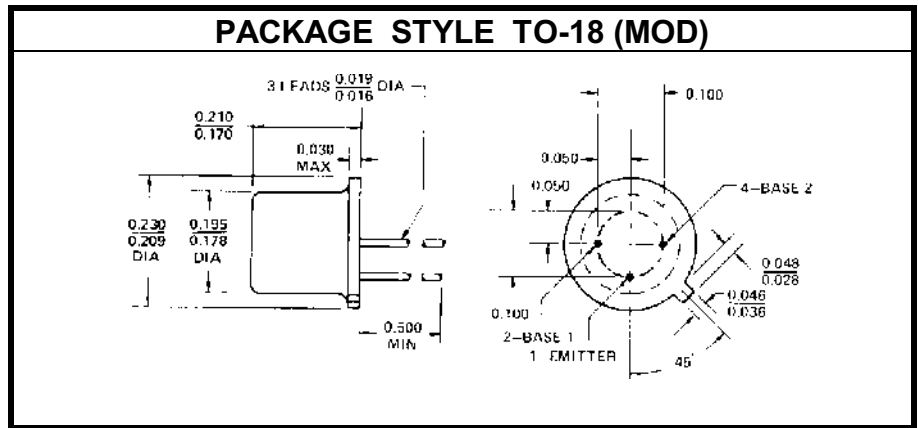
SILICON PN UNIJUNCTION TRANSISTOR

DESCRIPTION:

The **2N2646** is a Unijunction Transistor Used in General Purpose Pulse, Timing, Sense and Trigger Applications.

MAXIMUM RATINGS

I_C	2.0 A (PULSED)
V_{CE}	30 V
P_{DISS}	300 mW @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+125^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	33°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
η	$V_{B2B1} = 10\text{ V}$	0.56		0.75	--
r_{BB}	$V_{B2B1} = 3.0\text{ V}$	4.7		9.1	$K\Omega$
α_{rBB}	$V_{B2B1} = 3.0\text{ V}$ $T_A = -55\text{ to }125^\circ\text{C}$	0.1		0.9	$\%/^\circ\text{C}$
$V_{EB1(SAT)}$	$V_{B2B1} = 10\text{ V}$ $I_E = 50\text{ mA}$		3.0		V
$I_{B2(MOD)}$	$V_{B2B1} = 10\text{ V}$ $I_E = 50\text{ mA}$		20		mA
I_{B2EO}	$V_{B2E} = 30\text{ V}$ $I_{B1} = 0$			12	μA
I_P	$V_{B2B1} = 25\text{ V}$			5.0	μA
I_V	$V_{B2B1} = 20\text{ V}$ $R_{B2} = 100\ \Omega$	4.0			mA
V_{OB1}	$V_{B2B1} = 20\text{ V}$ $R_{B1} = 20\ \Omega$	3.0	5.0		V